

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Please amend the claims as follows:

Claim 1 (Currently amended): A fluorescent thin film comprising a matrix material which comprises a rare earth sulfide or a rare earth selenide, and which further comprises a rare earth element as a light emission center, the rare earth element as the light transmission center being different from the rare earth element of the matrix material, and

wherein said matrix material comprises at least one compound selected from the group consisting of a rare earth thioaluminate, a rare earth thiogallate and a rare earth thioindate, and wherein said rare earth element of the matrix material is an element selected from the group consisting of Y, La, Ce, Pr, Nd, Gd, Tb, Ho, and Er.

Claims 2-3 (Cancelled).

Claim 4 (Previously presented): The fluorescent thin film according to claim 1, wherein the matrix material is lanthanum thioaluminate or neodymium thioaluminate.

Claim 5 (Previously presented): The fluorescent thin film according to claim 1, wherein the rare earth element as the light emission center is at least one element selected from the group consisting of Ce, Eu, Tb and Tm.

Claim 6 (Previously presented): An EL panel comprising a fluorescent thin film according to claim 1.

Claim 7 (Withdrawn).

Claim 8 (Currently amended): The fluorescent thin film according to claim ~~8~~ 1, wherein the matrix material is at least one compound selected from the group consisting of

lanthanum thioaluminate, neodymium ~~thio~~gallate thiogallate and yttrium thioindate ~~and~~
~~Europium thioaluminate.~~

Claim 9 (New): A fluorescent thin film comprising a matrix material which
comprises a rare earth sulfide or a rare earth selenide, and which further comprises a rare
earth element as a light emission center, the rare earth element as the light transmission center
being different from the rare earth element of the matrix material, and
wherein said matrix material comprises at least one compound selected from the
group consisting of lanthanum thioaluminate and neodymium thioaluminate.

Claim 10 (New): The fluorescent thin film according to claim 9, wherein said rare
earth element added as said light emission center is one element selected from the group
consisting of at least Ce, Eu, Tb and Tm.

Claim 11 (New): An EL panel comprising a fluorescent thin film as recited in claim
9.

Claim 12 (New): A process of forming the fluorescent thin film according to claim 9
by an evaporation technique, wherein:

at least, a rare earth metal evaporation source and a group III sulfide evaporation
source with a light emission center added thereto are placed in a vacuum chamber with H₂S
gas introduced therein, and

a rare earth metal and a group III sulfide material are evaporated from the respective
evaporation sources to deposit a sulfide fluorescent thin film on a substrate while the
respective materials are combined with the H₂S gas.

Claim 13 (New): The fluorescent thin film according to claim 9, wherein the matrix material is at least one compound selected from the group consisting of lanthanum thioaluminate, neodymium thiogallate and yttrium thioindate.

Claim 14 (New): A fluorescent thin film comprising a matrix material which comprises a rare earth sulfide or a rare earth selenide, and which further comprises a rare earth element as a light emission center, the rare earth element as the light transmission center being different from the rare earth element of the matrix material, and

wherein said matrix material comprises at least one compound selected from the group consisting of lanthanum thioaluminate, neodymium thiogallate and yttrium thioindate.

Claim 15 (New): The fluorescent thin film according to claim 14, wherein said rare earth element added as said light emission center is one element selected from the group consisting of at least Ce, Eu, Tb and Tm.

Claim 16 (New): An EL panel comprising a fluorescent thin film as recited in claim 14.

Claim 17 (New): A process of forming the fluorescent thin film according to claim 14 by an evaporation technique, wherein:

at least, a rare earth metal evaporation source and a group III sulfide evaporation source with a light emission center added thereto are placed in a vacuum chamber with H₂S gas introduced therein, and

a rare earth metal and a group III sulfide material are evaporated from the respective evaporation sources to deposit a sulfide fluorescent thin film on a substrate while the respective materials are combined with the H₂S gas.